

Material Efficiency: The case of devices for IoT

HIDEO OHNO

PROFESSOR AND DIRECTOR

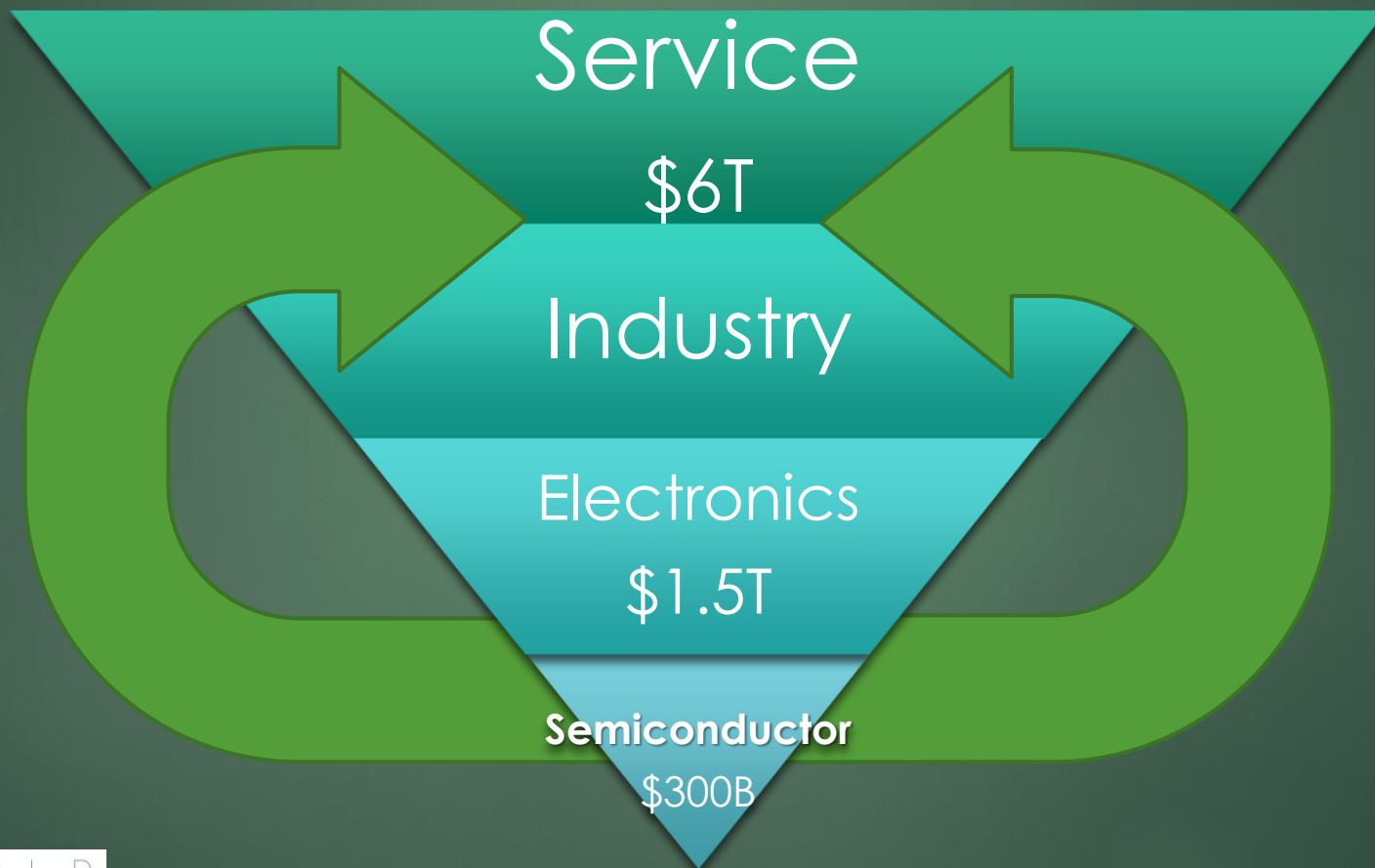
RESEARCH INSTITUTE OF ELECTRICAL COMMUNICATION

ALSO WITH CENTER FOR SPINTRONICS INTEGRATED SYSTEMS

TOHOKU UNIVERSITY, JAPAN

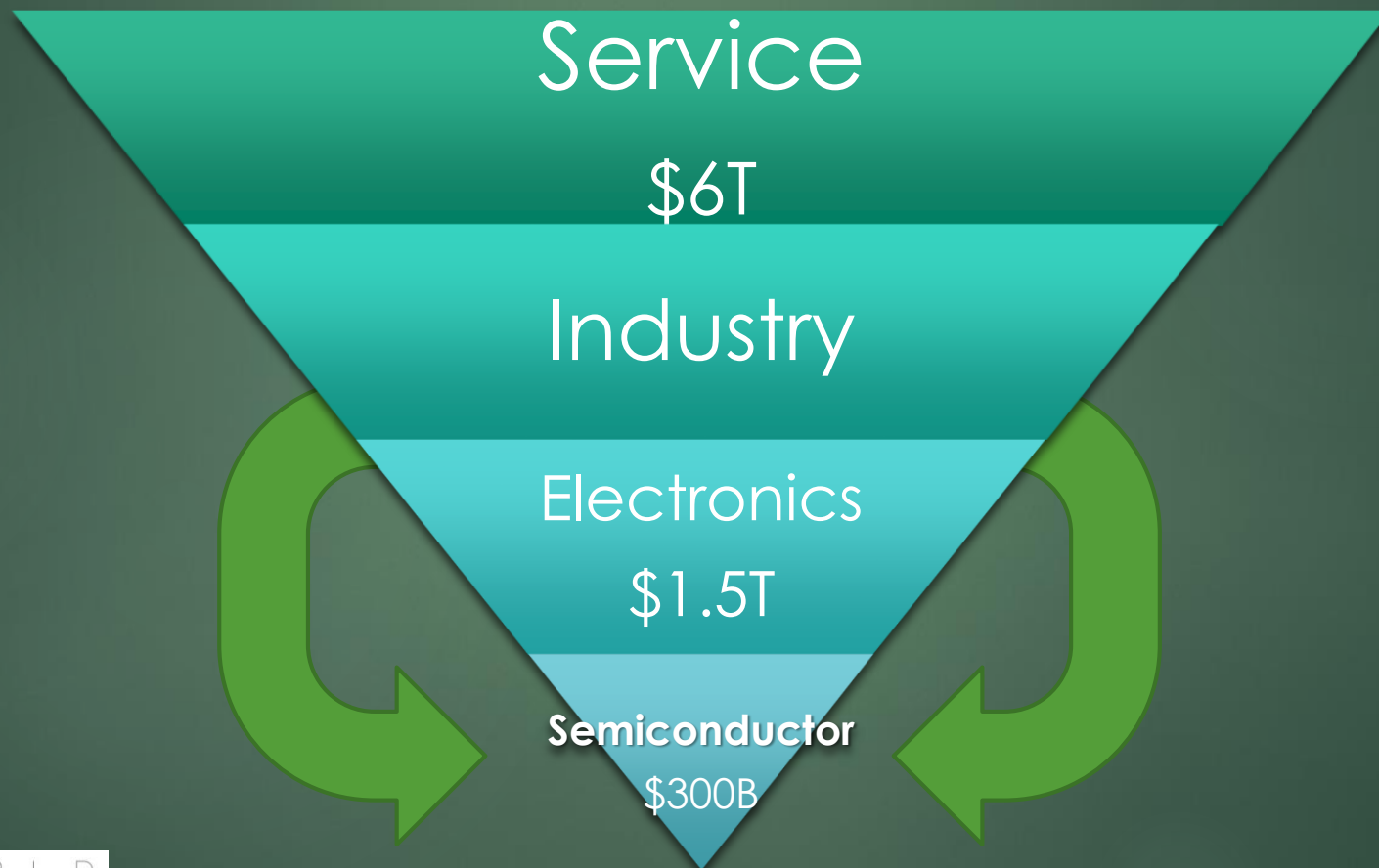
Market (a university professor's view)

2



Market (a university professor's view)

3



IoT Devices

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Sensors

Communication



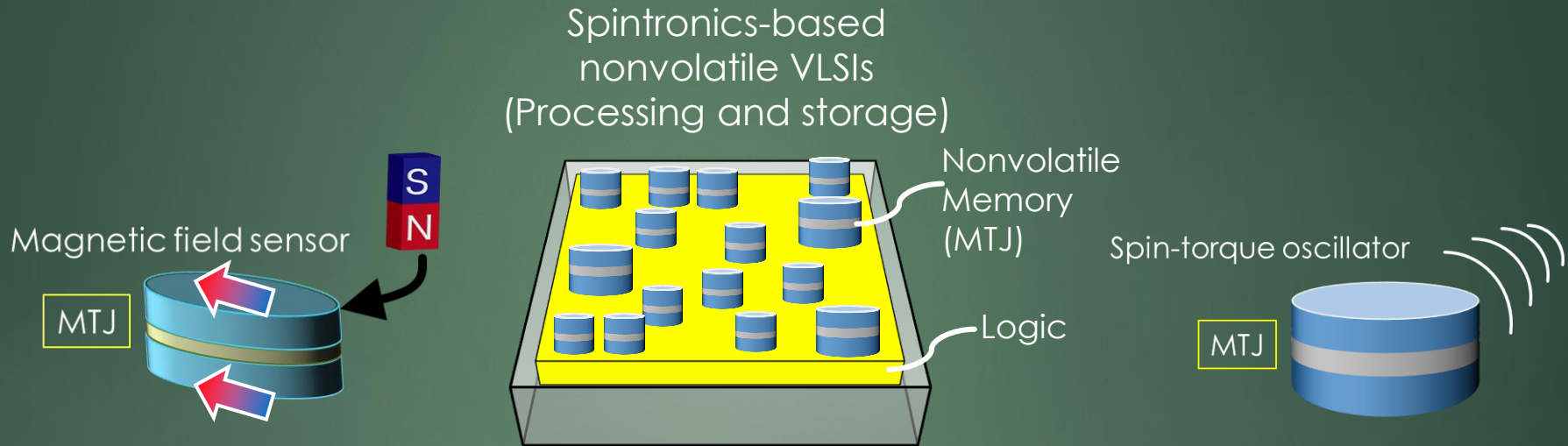
Storage

Processing

- ▶ Limited bandwidth: processed data for upload
- ▶ Maintenance free: energy efficiency
- ▶ IoT devices have to be
 - small = material efficient
 - smart = information processing capability
 - energy efficient = low power/standby power free

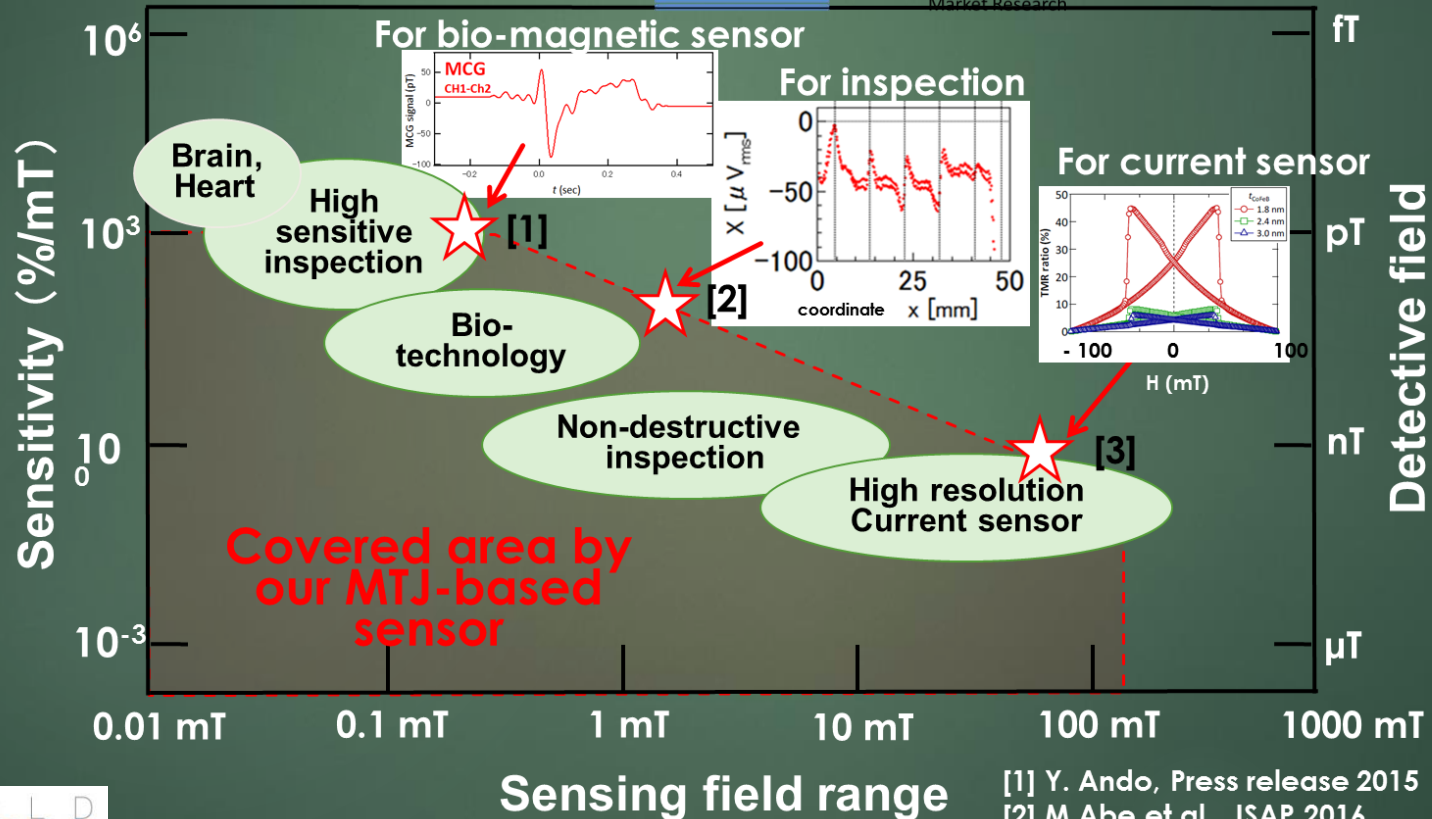
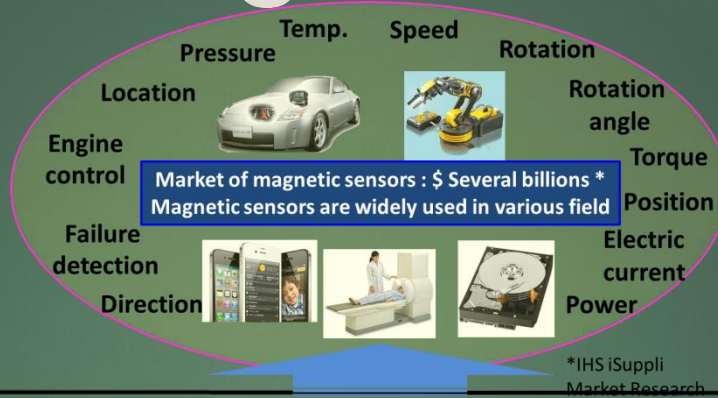
Spintronics does it all (Magnetic Tunnel Junction: MTJ)

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- ▶ Spintronics devices can
 - ✓ sense magnetic fields,
 - ✓ generate high frequency for communication, and
 - ✓ provides nonvolatile low-power processing
- ▶ They are **small** and can be made **nonvolatile**
- ▶ Magnetic Tunnel Junction (MTJ): key spintronics device

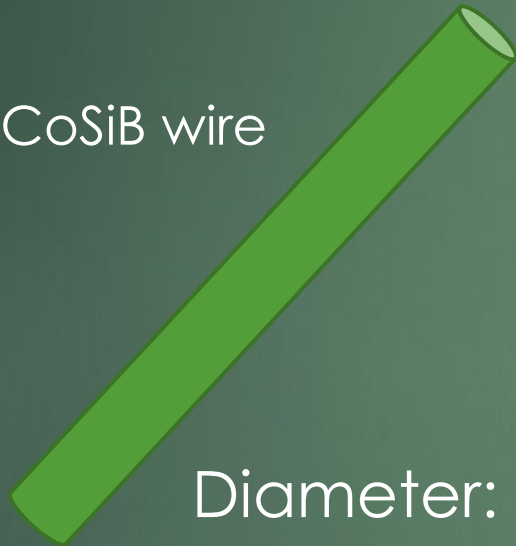
MTJ-based magnetic sensors



[1] Y. Ando, Press release 2015
[2] M.Abe et al., JSAP 2016
[3] T. Nakano et al., MMM 2016

MTJ based field sensor vs. MI sensors

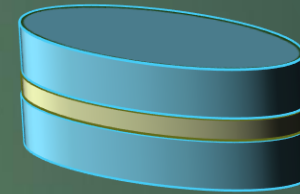
FeCoSiB wire



Diameter: $\sim 20 \mu\text{m}$

versus

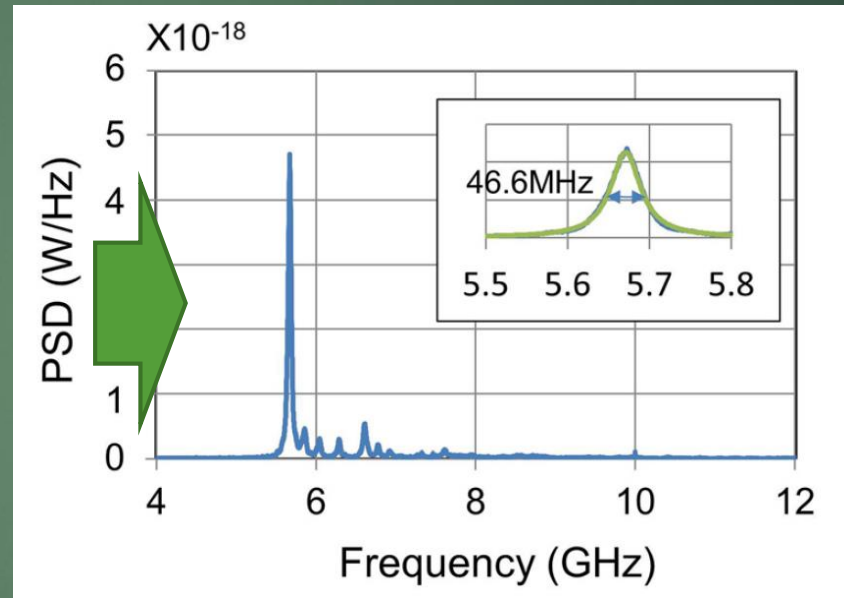
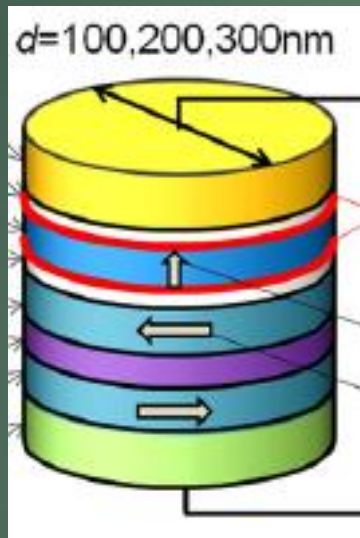
MTJ based magnetic
field sensor



Size: $\sim \mu\text{m}^2$

Taken from <http://www.aichi-mi.com/mi-technology/%E5%8E%9F%E7%90%86/> (Japanese)

High Frequency Generation and detection by Magnetic Tunnel Junction



Taken from S. Tamaru *et al.*, J. Appl. Phys. **115**, 17C740 (2014).

Crystal oscillator



Size: ~ mm

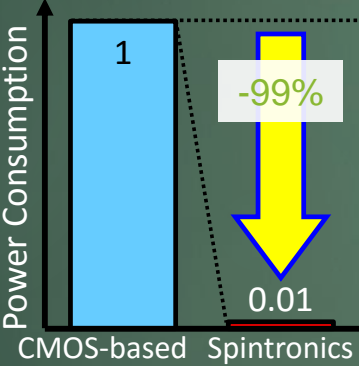
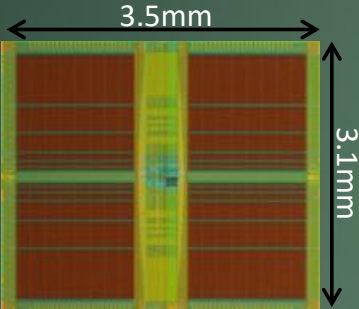
https://en.wikipedia.org/wiki/Crystal_oscillator

MTJ/CMOS Nonvolatile VLSIs

2013 Symposium. On VLSI Circuits

NV-TCAM

Non-volatile VLSIs for search engine for big data



$$1 \times \frac{1}{100} \times 1 \leq \frac{1}{64}$$

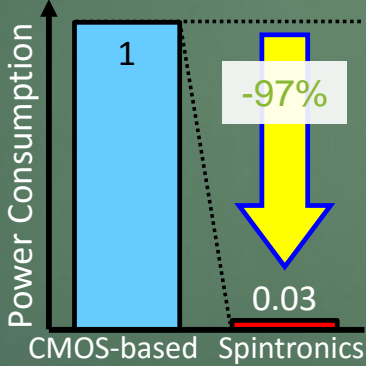
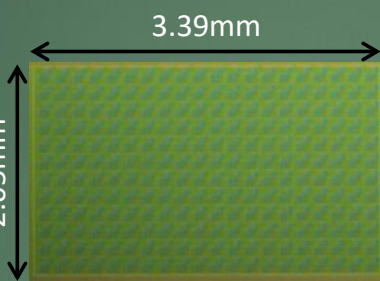
(delay) (power) (area)

※in case of used for full text search system

2013 IEICE Electronics Express

NV-FPGA

Non-volatile field programmable gate array (FPGA)



$$1 \times \frac{1}{32} \times \frac{1}{2} \leq \frac{1}{64}$$

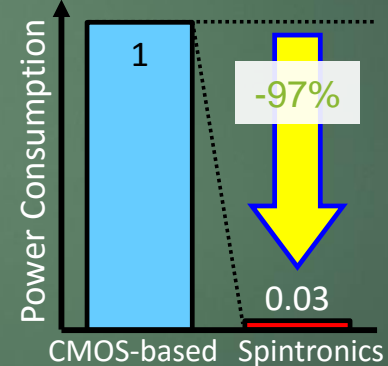
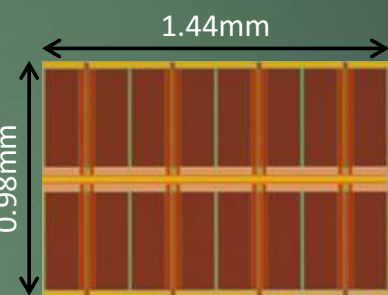
(delay) (power) (area)

※ in case of implementation to a typical application

2012 Symposium. On VLSI Circuits

STT-MRAM

Non-volatile cash memory embedded in high speed CPU



$$\frac{1}{1.5} \times \frac{1}{29} \times \frac{1}{1.7} \leq \frac{1}{64}$$

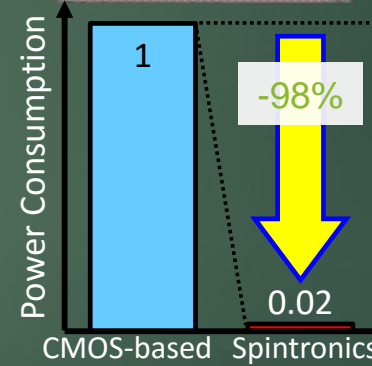
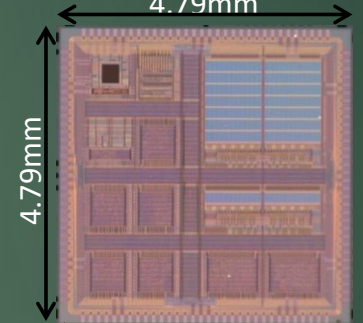
(delay) (power) (area)

※in case of typical cash operation

2014 IEEE ISSCC

NV-MPU

Non-volatile microcontroller for battery-driven sensor device



$$1 \times \frac{1}{80} \times 1 \leq \frac{1}{64}$$

(delay) (power) (area)

※in case of use in a wireless sensor device

Battery-free: Can we get there?

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Energy Harvesting

- 300 μW : Solar cell with room light
- 100 μW : Vibration

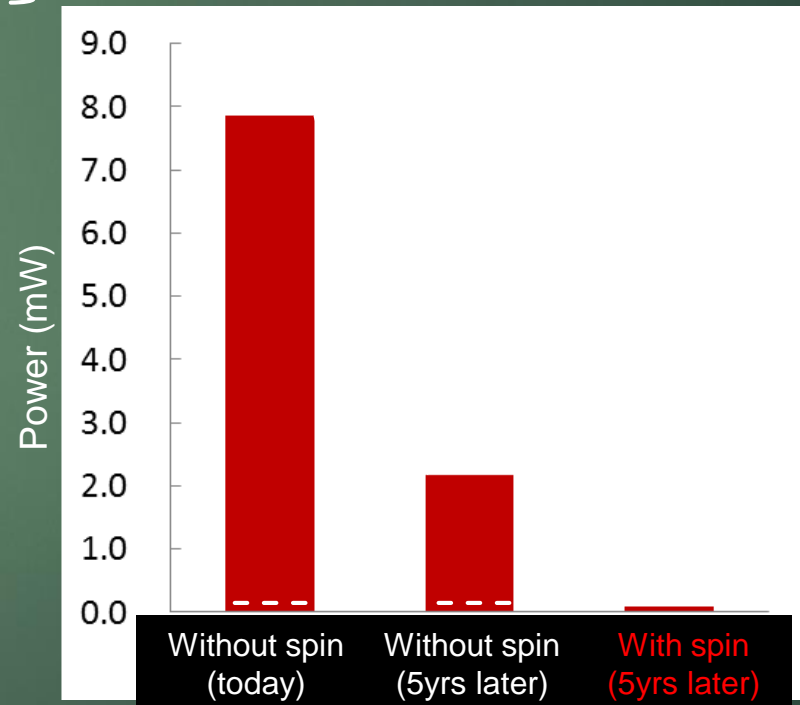
Intermittent Sensing

- 10 \times 10 sec-sensing a day

Distribution of Power

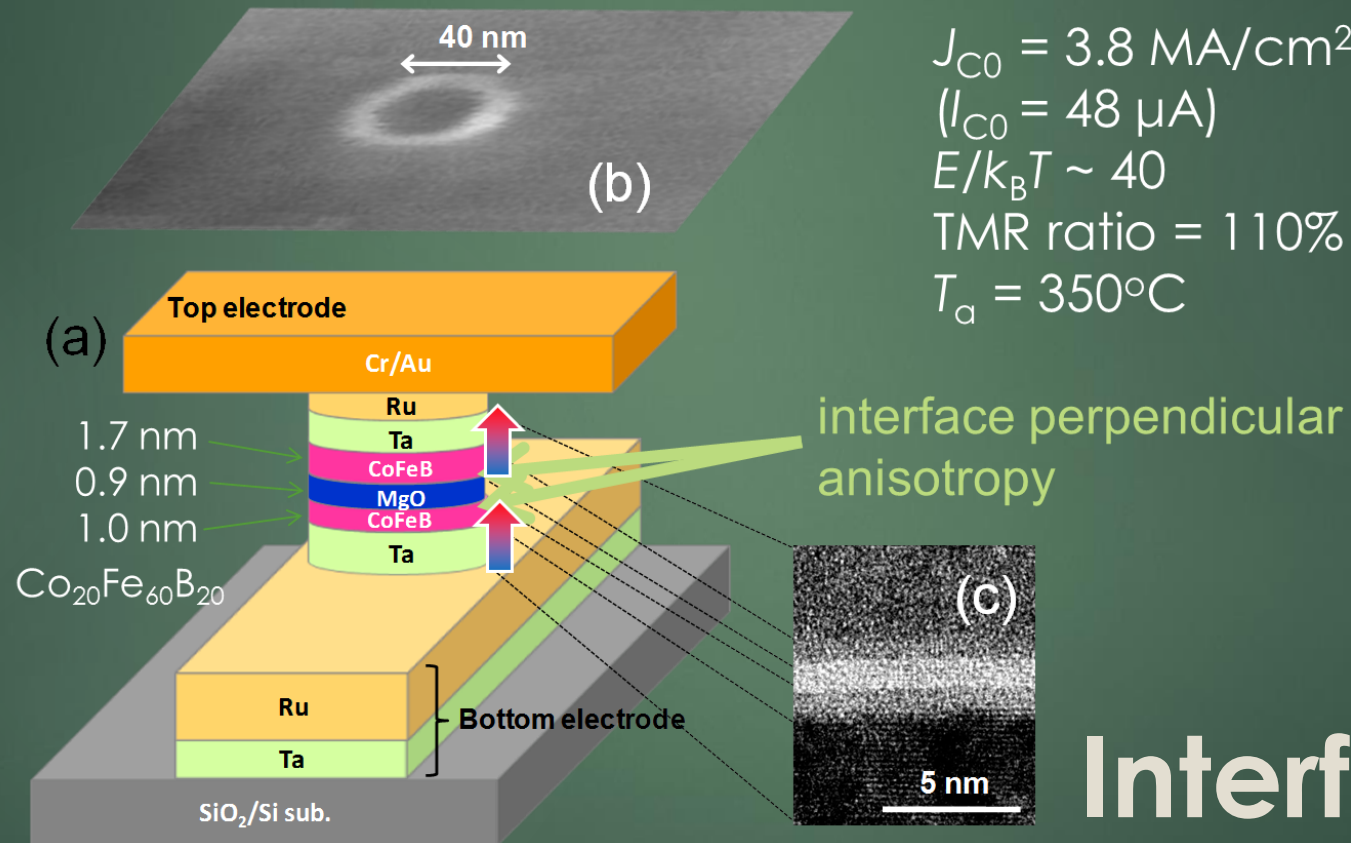
- 200 μW
 - Sensing: 20 μW
 - RF: 80 μW
 - Microcontroller: 100 μW

} 200 μW



High performance nonvolatile memory element:

Perpendicular MgO-CoFeB MTJ

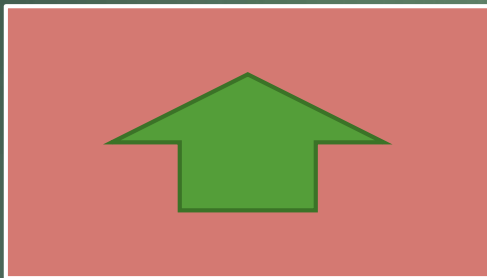


Interface!

Magnetic Tunnel Junction - bulk versus interface -

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FePt (bulk)



CoFeB (interface)

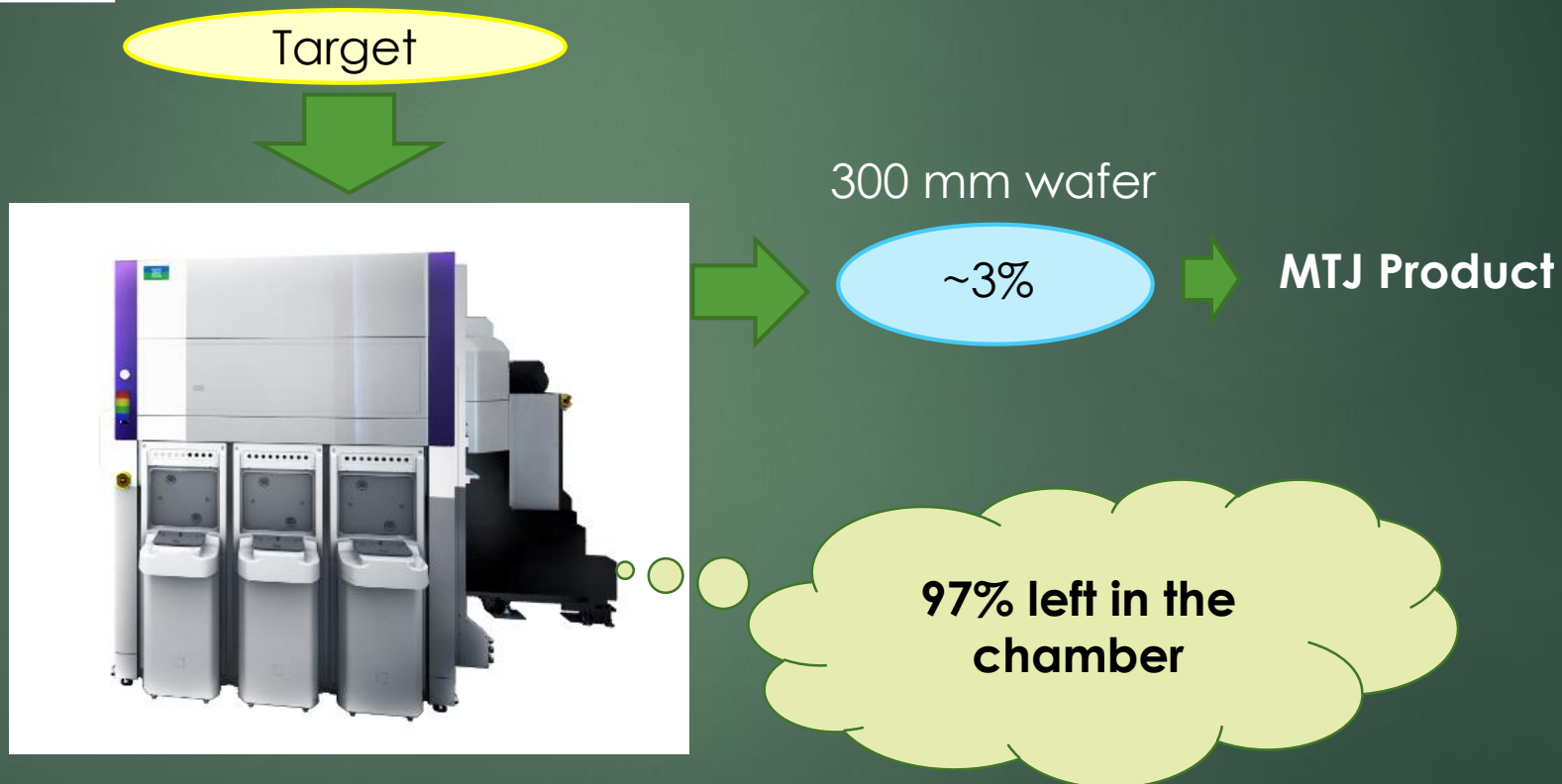


Materials Efficiency (Cost of material)

10 : 1

Recycling at the level of manufacturing tool: efficiency

MTJ Material



http://www.tel.co.jp/news/2014/1201_001.htm

SUMMARY

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- ▶ **Spintronics device** (Magnetic Tunnel Junction) provides key functionalities required for IoT: sensing, communication, and information processing/storage
- ▶ It is material efficient and becoming more so with newly developed device structure (**interface**)
- ▶ **Retrieving unused materials** from manufacturing tools under development for further increasing the material efficiency